

Notice of References Cited	Application/Control No. 10/549,859		Applicant(s)/Patent Under Reexamination KOBAYASHI ET AL.	
	Examiner MICHAEL G. MILLER		Art Unit 1792	Page 1 of 1

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*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
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*	C	US-6,093,457 A	07-2000	Okumura et al.	427/569
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NON-PATENT DOCUMENTS

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*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
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